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## Saveliev

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# (54) AVALANCHE PIXEL SENSORS AND RELATED METHODS

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#### Related U.S. Application Data

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- (52) **U.S. Cl.** ...... **250/370.01**; 250/208.1; 250/204; 250/214 R

## (56) References Cited

### U.S. PATENT DOCUMENTS

7,238,943	B2*	7/2007	Wong et al 250/367
2005/0012033	A1	1/2005	Stern et al.
2005/0139777	A1*	6/2005	Rostaing et al 250/394
2008/0156993	A1	7/2008	Weinberg et al.
2008/0203309	A1*	8/2008	Frach et al 250/362
2011/0233413	A1*	9/2011	Prescher et al 250/370.01

#### OTHER PUBLICATIONS

Golovin et al. Novel type of avalanche photodetector with Geiger mode operation; 2004; Nuclear Ins. and Methods in Phys. Re A 518 560-654.\*

Moehrs et al.; A detector head design for small-animal PET with silicon photomultipliers (SiPM); Feb 9. 2006; Phys. Med. Biol. pp. 1-17\*

Claus, et al., Monolithic active pixel sensors for a linear collider, Nuclear Instruments and Methods in Physics Research A 473 (2001) 83-85.

Chaubaud, et al., The DELPHI silicon strip microvertex detector with double sided readout, Nuclear Instruments and Methods in Physics Research A 368 (1996) 314-332.

Turchetta, ,CMOS Monolithic Active Pixel Sensors (MAPS) for future vertex detectors, SNIC Symposium, Stanford, Cal., (Apr. 2006) 1-4.

## \* cited by examiner

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## 57) ABSTRACT

According to an embodiment, an avalanche pixel sensor includes a substrate having opposite first and second surfaces, first sensor elements operating in breakdown mode situated on the first surface of the substrate for detecting ionizing radiation from a radiation-emission source, second sensor elements operating in breakdown mode situated on the second surface of the substrate, the second sensor elements each paired with a corresponding first sensor element to experience substantially coincident breakdown in response to ionizing radiation. Logic elements are each electrically interconnected to a respective pair of first and second sensor elements for receiving a signal or signal representing the substantially coincident breakdown of the respective pair to be distinguished from a dark signal even in either of the pair of the first and second sensor elements. Additionally, a detector array, a sensing apparatus, and a method of detecting ionization radiation using first and second sensor elements disposed on opposite sides of a substrate are also provided.

### 25 Claims, 7 Drawing Sheets

